Silicon NPN Power Transistors 2SC1828

DESCRIPTION

- With TO-66 package
- Continuous collector current-I_C=1A
- Power dissipation –P_C=40W @T_C=25℃

APPLICATIONS

- For power amplifier applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		1	A
P_T	Total power dissipation	T_C=25℃	40	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ; I_B=0	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ; I_E=0	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1A; I_B=0.2A			1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=1A; I_B=0.2A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=800V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=0.2A ; V_{CE}=10V	30		200	
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V		10		MHz

PACKAGE OUTLINE

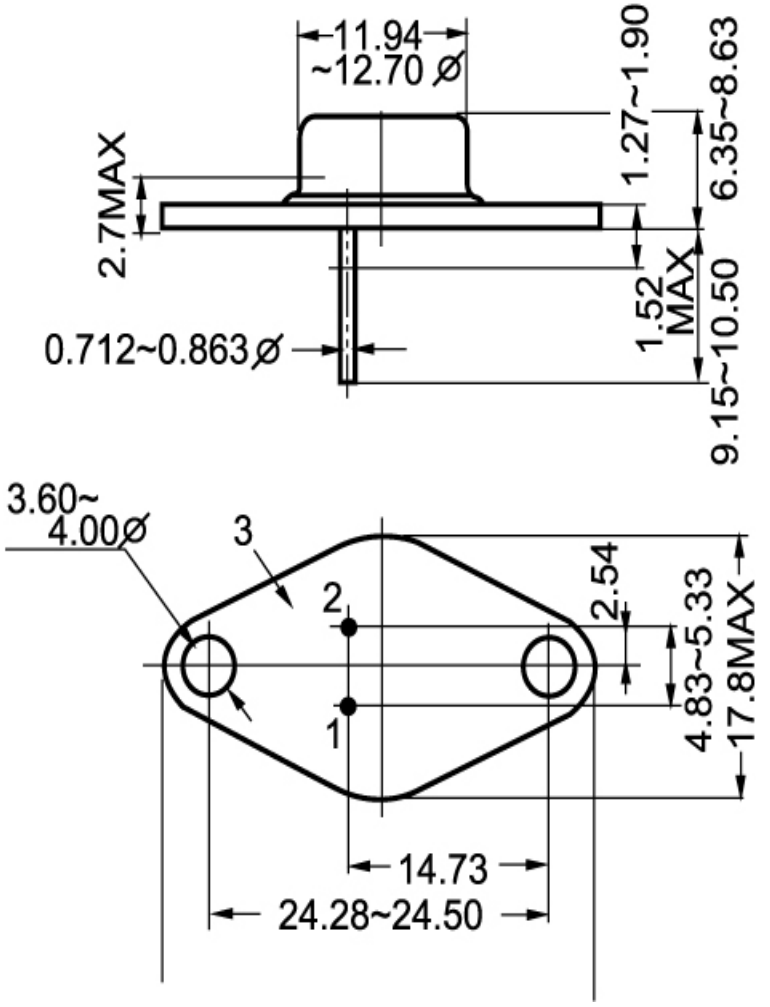


Fig.2 Outline dimensions